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Cite this: Phys. Chem. Chem. Phys., 2020, 22, 2429

The intrinsic magnetism, quantum anomalous Hall effect and Curie temperature in 2D transition metal trihalides[†] HPSTAR 907-2020

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Searching for experimentally feasible intrinsic quantum anomalous Hall (QAH) insulators is of great significance for dissipationless electronics applications. Here we predict, based on density functional theory (DFT), that four monolayer transition metal tri-bromides (VBr₃, FeBr₃, NiBr₃, and PdBr₃) are endowed with intrinsic half-metallicity and possess quantum anomalous Hall insulating phases. DFT+*U* calculations reveal that the VBr₃, NiBr₃, and PdBr₃ monolayers undergo nontrivial to Mott insulator transitions with increasing on-site Hubbard Coulomb interaction *U* at 0.5, 2 and 3 eV. The gap opening induced by the spin–orbit coupling drives the systems into the QAH state. The Curie temperatures of the VBr₃, NiBr₃, and PdBr₃ monolayers are ~190, 100 and 110 K. Additionally, the calculated cleavage energies suggest that the free-standing VBr₃, FeBr₃, NiBr₃, and PdBr₃ monolayers can be easily produced by exfoliation using adhesive tape, which may stimulate experimental research interest to achieve QAH phases.

Received 15th September 2019, Accepted 3rd January 2020

DOI: 10.1039/c9cp05084a

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Introduction

The quantum anomalous Hall (QAH) effect, arising from timereversal symmetry broken *via* internal magnetization, was first proposed by Haldane in a 2D honeycomb lattice.¹ Unfortunately, not much progress towards the realization of the QAH effect has been made because the host material of the 2D honeycomb-lattice was believed to be unrealistic up until graphene was successfully exfoliated in 2004.² The experimental realization of graphene not only raised the hope of achieving the QAH effect in a real 2D honeycomb-lattice system,^{3–5} but also made the era of 2D materials come.^{6–8}

Recently, this long-sought QAH effect has been predicted in graphene by adsorbing transition metal atoms or proximity coupling to a ferromagnetic (FM) or anti ferromagnetic (AFM) insulator,^{9–13} and experimentally observed in V- or Cr-doped (Bi, Sb)₂Te₃ topological insulators.^{14–17} Realization of QAH phases is of great significance both in fundamental physics and in dissipationless electronics applications.^{18,19}

Despite the numerous theoretical predictions and experimental studies, there are limitations for the current study of real QAH materials. The QAH phase in graphene decorated with heavy adatoms has not been realized thus far.^{20,21} Actually, introducing long-range FM order by doping in insulating films is quite a tough task in carrying out experiments with the QAH effect.²² In addition, the synthesis of such thin films based on molecular beam epitaxy is expensive and difficult to manipulate. Thus, recent efforts^{23–27} have focused on searching for experimentally feasible intrinsic QAH insulators.

Very recent experimental discoveries of intrinsic two dimensional (2D) ferromagnetic semiconductors^{28,29} have received much attention, not only of experimentally feasibility²⁸ but also of internal ferromagnetism,^{25,26,30–33} which might achieve the highly desirable QAH effect. It has been theoretically predicted that several 2D transition-metal tri-halides can host the QAH effect, such as RuI₃,³⁴ ReX₃³⁵ (X = Br, I), and MnX₃³⁶ (X = F, Cl, Br, I). And, more importantly, 3D layered crystals with weak interlayer van der Waals interactions are easily exfoliated down to 2D monolayers.^{37–39}

Here we studied 14 transition metal tri-bromide monolayers based on first principles calculations, and found that VBr₃, FeBr₃, NiBr₃, and PdBr₃ are endowed with intrinsic half-metallicity and possess QAH insulating phases. Nontrivial states emerge of VBr₃, NiBr₃, and PdBr₃ at the Fermi level when U < 0.5, 2, and 3 eV. Upon further increasing the effective on-site Hubbard Coulomb interaction, they undergo a transition from the nontrivial to the Mott insulating state. The topological nontrivial properties of monolayer VBr₃ were identified by calculations of the Berry

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[†] Electronic supplementary information (ESI) available. See DOI: 10.1039/c9cp05084a

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curvature and the corresponding edge states. Besides, the Curie temperature is ~190, 100 and 110 K for VBr₃, NiBr₃ and PdBr₃ and the Néel temperature of FeBr₃ is calculated to be 70 K.

Computational methods

Our first-principles calculations are based on density functional theory (DFT)⁴⁰ as implemented in the Vienna ab initio simulation package (VASP).⁴¹ The external potential is given by the projector augmented-wave (PAW) approximation,42 and the exchangecorrelation functional is given by the generalized gradient approximation parameterized by Perdew, Burke, and Ernzerhof (GGA-PBE).⁴³ The electron-ion interaction was described by projector augmented-wave potentials, with 4p⁶3d⁴4s¹ and 4s²4p⁵ configurations treated as the valence electrons of V and Br, respectively. The plane-wave cutoff energy is set to be 500 eV in all first-principles calculations, and the first Brillouin zone is sampled using a Γ -centered (11 \times 11 \times 1) Monkhorst-Pack grid.⁴⁴ The convergence criteria for energy and the ionic force were set to 10^{-5} eV and 0.01 eV Å⁻¹, respectively. Sufficient vacuum was used along the z direction, *i.e.* perpendicular to the 2D sheet, to avoid spurious interaction among the periodic images. SOC was included in the self-consistent calculations. The effective Hubbard U term is considered to address the selfinteraction error of the generalized gradient approximation.⁴⁵ The dynamic stability of monolayer VBr₃ was verified by phonon dispersion analyses through the direct supercell method, as implemented in the PHONOPY code. Ab initio molecular dynamics (AIMD) simulations were performed with the Nosé-Hoover thermostat to confirm the thermal stability. Based on the Wannier functions⁴⁶ obtained from the first-principles calculations, we constructed the edge Green's function of the semi-infinite VBr₃ monolayer. The Berry curvature was calculated by Wannier interpolation. In order to integrate the Berry curvature, a much denser k mesh of $(120 \times 120 \times 1)$ was adopted.

Results and discussions

A. Structure and electronic structures of monolayer transition metal tri-bromides

In reality, transition metal tri-halides MX_3 (M is a metal cation and X is a halogen anion) have been reported to adopt either the monoclinic AlCl₃ structure type or the rhombohedral BiI₃ structure type,⁴⁷ as illustrated in Fig. 1. The monolayer structure of transition metal tri-bromides is composed of a honeycomb net of M metal cations that are in edge sharing octahedral coordination, derived from the bulk. In the octahedral coordination environments of the M atoms, the electronic and magnetic properties can be tuned by their electron configuration. The electronic structures of the transition metal tri-bromides we considered in this study using the PBE functional are shown in Fig. S1 and S2 (ESI[†]). We can find that (1) most of the transition metal tri-bromides are ferromagnetic except nonmagnetic CoBr₃ and RhBr₃; (2) most of the ferromagnetic materials are halfmetallic except semiconductors CrBr₃ and MoBr₃; (3) most of



Fig. 1 A side view of (a) the Bil₃ and AlCl₃ structure types and (b) a plan view of common monolayers with coordinate systems corresponding to each structure type. (c) The phonon band structure of monolayer VBr₃.

the half-metallic materials can host a Dirac point except ZrBr₃; and (4) the spin-polarized massless Dirac fermions of VBr₃, FeBr₃, NiBr₃ and PdBr₃ are found at the high-symmetry *K* point of the Brillouin zone. Then, we focus on further analyzing the structural characteristics, and electronic and magnetic properties of VBr₃, FeBr₃, NiBr₃ and PdBr₃.

B. Structure and stability

The optimized structures of the MBr₃ (M = V, Fe, Ni, and Pd) monolayers are composed of a Br–M–Br sandwich where a sheet of M atoms is sandwiched between two sheets of Br atoms. The unit cell is composed of two M atoms and six Br atoms, and M is in octahedral coordination with Br atoms. The corresponding lattice constants and bond lengths of VBr₃, FeBr₃, NiBr₃ and PdBr₃ are listed in Table 1. We have studied the lattice dynamics adopting (3×3) supercells by calculating the phonon dispersions. As presented in Fig. 1c, the absence of imaginary modes in the entire Brillouin zone confirms that monolayer VBr₃ is dynamically stable. Note that the FeBr₃, NiBr₃, and PdBr₃ monolayers are also dynamically stable.^{48–50} After heating at room temperature (300 K) with a time step of 1 fs, no structure reconstruction is found to occur, indicating that they are also thermodynamically stable. The snapshots of the atomic configurations of the VBr₃,

Table 1 The optimized lattice constants (α , Å) and bond lengths (d, Å), and thickness (h, Å) of VBr₃, FeBr₃, NiBr₃ and PdBr₃ at the PBE level. The "thickness" of this monolayer is defined as the distance between the vertical coordinates of the top-Br layer and the bottom-Br layer

Compounds	α	$d_{ m Br-M}$	h
VBr ₃	6.61	2.54	2.92
FeBr ₃	6.36	2.45	2.80
NiBr ₃	6.30	2.45	2.81
PdBr ₃	6.67	2.57	2.87

FeBr₃, NiBr₃, and PdBr₃ monolayers at the end of the AIMD simulations are shown in Fig. S3 (ESI \dagger). Moreover, we have performed a first-principles swarm structural search^{51,52} and found that the structure in Fig. 1(b) is the global minimum.

C. Experimental feasibility

The weak van der Waals interaction in the layered bulk crystals allows monolayer transition metal tri-bromides to be obtained from the crystal using mechanical exfoliation. To obtain a free-standing membrane, the cleavage energy needed to be overcome in the exfoliation process should be small. A large gap *d* between two layers representing a fracture in the bulk is introduced to simulate the exfoliation procedure. The cleavage energies as a function of *d* calculated using the optB86b-vdW functional are shown in Fig. 2. It can be seen that the cleavage energies for the VBr₃, FeBr₃, NiBr₃, and PdBr₃ materials are 0.28, 0.12, 0.14, and 0.17 J m⁻², significantly smaller than that of MoS₂ (0.27 J m⁻²) and graphite (0.37 J m⁻²).⁵³ Thus, free-standing VBr₃, FeBr₃, NiBr₃, and PdBr₃ monolayers can be easily produced by exfoliation using adhesive tape.

D. Electronic properties and Curie temperature

The values of the M–Br–M angles for VBr₃, FeBr₃, NiBr₃, and PdBr₃ are 97.42°, 95.89°, 95.90° and 97.00°. According to the Goodenough–Kanamori–Anderson (GKA) rules the superexchange interaction of a 90° cation–anion–cation angle favors FM ordering whereas a 180° angle favors antiferromagnetic.^{54,55} Thus, the superexchange interactions between two nearest-neighbor M atoms mediated by Br are expected to be dominant leading to an FM ground state. We consider four possible magnetic configurations (one FM and three AFM) to determine the optimal magnetic coupling, as shown in Fig. S4 (ESI†), and calculate the energy difference between the ferromagnetic and antiferromagnetic states, listed in Table S1 (ESI†). The FM states in VBr₃, NiBr₃ and PdBr₃ have the lowest total energy and an AFM state in FeBr₃ has the lowest total energy. One of the important

properties of ferromagnets and antiferromagnets is the Curie temperature and Néel temperature. Using Monte Carlo (MC) simulations based on the 2D Ising model, we have calculated the Curie temperature of VBr₃, NiBr₃ and PdBr₃ and the Néel temperature of FeBr₃. For simplicity, only the nearest neighbor (NN) exchange interaction is considered since the second and third NN exchange interactions are smaller than the first NN exchange interactions.³⁶ The NN exchange-coupling parameters *J* can be extracted by mapping the total energies of the systems with different magnetic structures to the Ising model:

$$H = -\sum_{ij} JS_i \cdot S_j$$

where *S* is the net magnetic moment at the M site, and *i* and *j* represent the nearest M atoms. By comparing the total energies of ferromagnetic and antiferromagnetic states (E_{ex}), the exchange parameter can be evaluated by $J = E_{ex}/6S^2$; we obtain J = 9.2, 19 and 20 meV for VBr₃, NiBr₃ and PdBr₃. For FeBr₃, the exchange parameter is -13 meV. A positive/negative value represents FM/ AFM coupling. The calculated Curie temperature is ~ 190 , 100 and 110 K (Fig. 3) for VBr₃, NiBr₃ and PdBr₃, which is comparable with that of other 2D FM materials.^{35,56,57} The Néel temperature is calculated to be 70 K.

It is widely accepted that the magnetocrystalline anisotropic energy (MAE) closely correlates with the thermal stability of magnetic data storage of a magnetic material. In general, the larger the MAE, the better the performance for data storage. Here, two magnetization directions in plane, that is the [110] and [1-10] directions, and one direction out of plane, that is the [001] direction, are considered, as summarized in Table S2 (ESI†). Among them, the in-plane [110], [1-10], and [110] directions for VBr₃, NiBr₃ and PdBr₃ are the easy axis, respectively.

The band structure of the FM ground state for the VBr_3 monolayer is shown in Fig. 4(a). VBr_3 can be approximately characterized as a "zero-gap half-metal" in the case without



Fig. 2 Supercell model used to simulate the exfoliation procedure and the cleavage energy calculated using the optB88-vdW functional as a function of the separation d between the two fractured parts. d_0 represents the equilibrium interlayer distance.



spin–orbit coupling (SOC). It has almost zero gap because of the band-toughing at the high-symmetry *K* point just above the Fermi level in the spin-up channel. It is nearly a half-metal because of the presence of a band gap of 2.85 eV in the spindown channel. The Dirac states of VBr₃ are mainly derived from the V-d orbitals. The SOC opens a band gap of 20 meV for VBr₃ (Fig. 4a). Because the GGA usually underestimates the band gap, the HSE06 hybrid functional is also used to check the band gaps. Our calculations show that the band gap is 48 meV with HSE06 for the VBr₃ monolayer, as seen in Fig. 4b. As shown in Fig. S1 (ESI[†]), the FeBr₃, NiBr₃ and PdBr₃ monolayers also have almost zero gaps because of the band-toughing at the highsymmetry *K* point. However, they are semiconducting taking the HSE functional into consideration [Fig. S5, ESI[†]].

The projected density of states (PDOS) and the projected band structures were calculated for the VBr₃ monolayer at the PBE level to gain insight into the origin of the electronic and magnetic properties (Fig. 5). Under the distorted octahedral crystal field of Br atoms, the d orbital of V would be split into one a₁ orbital corresponding to the d_{z²} orbital and two e1 and e2 orbitals corresponding to the (d_{xz}, d_{yz}) and (d_{x²-y²}, d_{xy}) orbitals. The two d electrons with spin-up lead to partially filled d orbitals, giving rise to the metal character and exhibiting a high-spin a^{1†}e^{1†}₂e^{1†}₀a^{0†}e^{0†}₂e^{0†}₁ electronic configuration. Based on Griffith's crystal field theory, the spin states of transition metal ions can be determined by the relative strength between crystal field splitting (ΔE_{cf}) and Hund exchange splitting (ΔE_{ex}) of d orbitals. The exchange splitting (0.96 eV) and the crystal field splitting (0.89 eV) for the VBr₃ monolayer lead to a high spin (2 μ_B) state, which is in good agreement with the V ($a^{1\dagger}e_2^{1\dagger}e_1^{0\dagger}a^{0\dagger}e_2^{0\dagger}e_1^{0\dagger}$) spin configuration. The calculated magnetic moment of the V atom is 1.97 μ_B per atom, which is consistent with the 2 μ_B per atom staying in the high-spin state. Because of the hybridization with V-3d states, the Br-4p are slightly spin polarized but with an opposite moment (about $-0.05 \ \mu_B$ per atom). Allowing for the delocalized feature of the Br 4p states, the FM structure between the V spins is expected to emerge in a long range.

The states near the Fermi level have main contributions from the a_1 and e_2 states, while the e_1 state does not contribute significantly as shown in Fig. 5a. The whole occupied a_1 and partially occupied e_2 orbitals around the Fermi level form a Dirac point in the VBr₃ monolayer. The zero gap behavior in the up spin channel is the most important characteristic here, because it suggests an inverted band structure around the high symmetry *K* point. The V ion has a strong ferromagnetic ground state, leading to strong Zeeman splitting for energy states near the Fermi level. The presence of exchange splitting means that the band inversion of the spin-up states occurs while the spin-down energy states maintain the normal band structure.

(a) 0.2 0. Energy (eV) Energy (eV) -0. with SOC -0.2 K M M 0.2 **(b)** 0.1 Energy (eV) Energy (eV) -0. with SO -0.2 ĸ м Fig. 4 Spin-polarized band structures of monolayer VBr₃ without and

Fig. 4 Spin-polarized band structures of monolayer VBr_3 without and with SOC at the (a) PBE and (b) HSE06 level. Inset: Dirac states near the Fermi level. The red and green lines represent the spin up and spin down channels, respectively.

In the down spin channel, the a_1 orbital level is higher than the e_2 orbital level. In sharp contrast, band inversion occurs between the a_1 state and e_2 orbital level in the up spin channel, as evidenced by the projected band structures in Fig. 5(b).

Next, we employ DFT+*U* calculations to show the effect of the on-site Coulomb repulsion *U* on the electronic structures of VBr₃, FeBr₃, NiBr₃ and PdBr₃ since the d electrons of a transition metal exhibit correlation effects, as shown in Fig. S6–S9 (ESI†). We can find that the *U* term greatly impacts the band structure of FeBr₃ and as the on-site Coulomb repulsion *U* gradually increases, the Mott insulating phases occur at *U* equal to 0.5, 2 and 3 eV in the VBr₃, NiBr₃, and PdBr₃ monolayers.

E. Quantum anomalous Hall effect

The existence of topologically protected chiral edge states is one of the most important consequences of the QAH state. To further reveal the nontrivial topological nature of the VBr₃ monolayer, we calculate the edge states of the VBr₃ monolayer using Green's functions based on Wannier functions obtained from PBE calculations, which reduces the cost of calculations while it does not change the topology of the electronic structure. As shown in Fig. 6, the nontrivial edge states connecting the valence and conduction bands cross the insulating gap of the Dirac cone, confirming the nontrivial topological nature of the VBr₃ monolayer. The Berry curvature along the high-symmetry direction ($\Gamma \rightarrow K \rightarrow M \rightarrow \Gamma$) has a sharp spike of the same sign located at the *K* and Γ points as shown in Fig. 6d. By integrating



Fig. 5 (a) The PDOS of d states for V atoms is shown. (b) The projected band structures without SOC (showing the up and down spin parts separately). The relative size of each symbol indicates the V atom projection of the eigenvalue. The Fermi level is set to zero.



Fig. 6 The edge states and the Berry curvature of monolayer VBr₃. The V spins are in (a) FM^x , (b) FM^y and (c) FM^z configurations. (d) The distribution of the Berry curvature in momentum space for VBr₃ based on the PBE method.

the Berry curvature in the entire Brillouin zone, the calculated Chern number C is -1 with a non-trivial topological state. As

expected from the non-zero Chern number, the anomalous Hall conductivity shows a quantized charge Hall plateau of $\delta_{xy} = e^2/h$ when the Fermi level is located in the insulating gap of the spin-up Dirac cone. The nontrivial topological properties of the FeBr₃, NiBr₃ and PdBr₃ monolayers have been verified.^{32,49,50}

Conclusions

Using DFT and DFT+U calculations, we have performed a systematic investigation of the electronic and magnetic structures in monolayer transition metal tri-bromides, especially those of the VBr₃, FeBr₃, NiBr₃ and PdBr₃ monolayers. Their Dirac spin-gapless half-metallic features are characterized by a band structure with an unusually large gap in one spin channel and a Dirac cone in the other spin channel at the PBE level. Upon increasing the on-site Coulomb repulsion, the VBr₃, NiBr₃ and PdBr₃ monolayers undergo a quantum phase transition from QAH insulator to Mott insulator. The calculated cleavage energies suggest that the freestanding VBr₃, FeBr₃, NiBr₃ and PdBr₃ monolayers can be easily obtained. Additionally, the Curie temperature is ~190, 100 and 110 K for VBr₃, NiBr₃ and PdBr₃. The Néel temperature of FeBr₃ is calculated to be 70 K. The combination of these unique properties renders monolayer transition metal tri-bromides a promising platform for potential applications in future spintronics.

Conflicts of interest

The authors declare no competing financial interest.

Acknowledgements

The authors acknowledge funding from the National Natural Science Foundation of China under Grant No. 11722433, 11904142, 11804128 and 11804129. All the calculations were performed using the High Performance Computing Center of the School of Physics and Electronic Engineering of Jiangsu Normal University.

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